



Low-Voltage Single SPDT Analog Switch

DESCRIPTION

The DG9411 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 9 ns, t_{OFF} : 5 ns), low on-resistance ($r_{DS(on)}$: 7 Ω) and small physical size (SC70), the DG9411 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG9411 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup. Break-before make is guaranteed for DG9411.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FEATURES

- Low voltage operation (2.25 V to 5.5 V)
- Low on-resistance $r_{DS(on)}$: 7 Ω
- Fast switching t_{ON}: 9 ns, t_{OFF}: 5 ns
- Low charge injection Q_{INJ}: 5 pC
- · Low power consumption
- TTL/CMOS compatible
- 6-Pin SC70 package

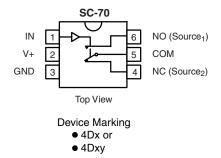
BENEFITS

- · Reduced power consumption
- · Simple logic interface
- High accuracy
- · Reduce board space

APPLICATIONS

- · Cellular phones
- · Communication systems
- · Portable test equipment
- · Battery operated systems
- · Sample and hold circuits

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE						
Logic	NC	NO				
0	ON	OFF				
1	OFF	ON				

 $\begin{array}{l} \text{Logic "0"} \leq 0.8 \ V \\ \text{Logic "1"} \geq 2.4 \ V \end{array}$

ORDERING INFORMATION					
Temp Range	Package	Part Number			
- 40 to 85 °C	SC70-6	DG9411DL-T1 DG9411DL-T1-E3			

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^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.



ABSOLUTE MAXIMUM RATINGS						
Parameter		Limit	Unit			
Reference V+ to GND		- 0.3 to + 6	V			
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	v			
Continuous Current (Any Terminal)		± 50	mA			
Peak Current (Pulsed at 1 ms, 10 % of	luty cycle)	± 200	IIIA			
Storage Temperature		- 65 to 150	°C			
Power Dissipation (Packages) ^b	6-Pin SC70 ^c	250	mW			

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board. c. Derate 3.1 mW/°C above 70 °C.

SPECIFICATIONS V+	= 2.5 V						
		Test Conditions Unless Otherwise Specified V+ = 2.5 V, ± 10 %		Limits - 40 to 85 °C			
Parameter	Symbol	$V_{IN} = 0.4 \text{ or } 2.0 \text{ V}^{e}$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit
Analog Switch			1			II.	
Analog Signal Range ^d	$V_{NO}, V_{NC} V_{COM}$		Full	0		V+	V
Drain-Source On-Resistance	r _{DS(on)}	$V+ = 2.25 \text{ V}, V_D = 1.0 \text{ V}, I_S = 10 \text{ mA}$	Room Full ^d		26 29	35 40	Ω
r _{DS(on)} Flatness ^d	r _{DS(on)} Flatness	V+ = 2.5 V	Room		10		32
Switch Off	I _{S(off)}	V+ = 2.75 V, V _S = 0.5 V/1.5 V, V _D = 1.5 V/0.5 V	Room Full ^d	- 250 - 3.0		250 3.0	pA nA
Leakage Current [†]	I _{D(off)}	V1 = 2.76 V, V5 = 0.6 V, 1.6 V, V _D = 1.6 V/0.6 V	Room Full ^d	- 250 - 3.0		250 3.0	pA nA
Channel-On Leakage Current ^f	I _{D(on)}	$V+ = 2.75 \text{ V}, V_S = V_D = 0.5 \text{ V}/1.5 \text{ V}$	Room Full ^d	- 250 - 3.0		250 3.0	pA nA
Digital Control							
Input High Voltage	V_{INH}		Full	2			V
Input Low Voltage	V_{INL}		Full			0.4	ľ
Input Capacitance ^d	C _{in}		Full		3		pF
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0$ or V+	Full	- 1		1	μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}	V 27V 15VD 2000 C 2575	Room Full ^d		16	40 45	
Turn-Off Time	t _{OFF}	V_D or V_S = 1.5 V, R_L = 300 Ω , C_L = 35 pF Figures 1 and 2	Room Full		7	23 28	ns
Break-Before-Make Time	t_d		Room ^d	1	12		
Charge Injection ^d	Q_{INJ}	C_L = 1 nF, V_{GEN} = 0 V, V_S = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	pC
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 1 MHz$	Room		- 73		dB
Crosstalk ^d	X _{TALK}	11[= 30 25 0[= 3 β1,1 = 1 10112	Room		- 70		ub
Source-Off Capacitance ^d	C _{S(off)}		Room		7		
Channel-On Capacitanced	C _{D(on)}	$V_{IN} = 0$ or V_{+} , $f = 1$ MHz	Room		20		pF
Drain-to-Source Capacitanced	C _{DS(off)}		Room		20		
Power Supply							
Power Supply Range	V+			2.25		2.75	V
Power Supply Current ^d	l+	V _{IN} = 0 or V+			0.01	1.0	μΑ
Power Consumption	P _C	IN = 0 01 V +				0.3	μW







SPECIFICATIONS V	+=3V							
		Test Conditions Unless Otherwise Specified $V+=3~V,\pm~10~\%$		-	Limits 40 to 85 °	°C	-	
Parameter	Symbol	$V_{IN} = 0.4 \text{ or } 2.0 \text{ V}^{e}$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit	
Analog Switch							1	
Analog Signal Range ^d	V_{NO}, V_{NC} V_{COM}		Full	0		V+	٧	
Drain-Source On-Resistance ^d	r _{DS(on)}	$V+ = 2.7 \text{ V}, V_D = 1.5 \text{ V}, I_S = 10 \text{ mA}$			15 19	25 30	Ω	
r _{DS(on)} Flatness ^d	r _{DS(on)} Flatness	$V_S = 0 \text{ to } V_{+}, I_S = 10 \text{ mA}$	Room		7.5		52	
Switch Off	I _{S(off)}	V+ = 3.3 V, V _S = 1 V/3 V, V _D = 3 V/1 V	Room Full	- 500 - 4.0		500 4.0	pA nA	
Leakage Current ^f	I _{D(off)}		Room Full	- 500 - 4.0		500 4.0	pA nA	
Channel-On Leakage Current ^f	I _{D(on)}	$V+ = 3.3 \text{ V}, V_S = V_D = 1 \text{ V/3 V}$	Room Full	- 500 - 4.0		500 4.0	pA nA	
Digital Control			1		•	•		
Input High Voltage	V _{INH}		Full	2			V	
Input Low Voltage	V _{INL}		Full			0.8	v	
Input Capacitanced	C _{in}		Full		3		pF	
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ	
Dynamic Characteristics			•		•	•		
Turn-On Time ^d	t _{ON}	V 01 V 00 V D 200 O C 25 pc	Room Full		12	15 20		
Turn-Off Time ^d	t _{OFF}	V_D or V_S = 2.0 V, R_L = 300 Ω , C_L = 35 pF Figures1 and 2	Room Full		6	8 10	ns	
Break-Before-Make Time ^d	t _d		Room	1	7			
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, V_S = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	pC	
Off-Isolation ^d	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 73		dB	
Crosstalk ^d	X _{TALK}	1 1 - 30 24 0 - 3 p1, 1 - 1 WILE	Room		- 70		ub	
Source-Off Capacitance ^d	C _{S(off)}		Room		7			
Channel-On Capacitance ^d	C _{D(on)}	$V_{IN} = 0$ or V_{+} , $f = 1$ MHz	Room		20		pF	
Drain-to-Source Capacitance ^d	C _{DS(off)}	IIV	Room		20		"	
Power Supply	•				•	•		
Power Supply Range	V+			2.7		3.3	V	
Power Supply Current	I+	$V_{IN} = 0$ or V+			0.01	1.0	μΑ	
Power Consumption	P _C	IIN 5 5 · · ·				0.4	μW	



		Test Conditions Unless Otherwise Specified		Limits - 40 to 85 °C			
		$V+ = 5 V, \pm 10 \%$					
Parameter	Symbol	$V_{IN} = 0.8 \text{ or } 2.4 \text{ V}^{e}$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit
Analog Switch							,
Analog Signal Range ^d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0		V+	V
Drain-Source On-Resistance	r _{DS(on)}	$V+ = 4.5 \text{ V}, V_D = 3 \text{ V}, I_S = 10 \text{ mA}$	Room Full		7 10	12 16	Ω
r _{DS(on)} Flatness ^d	r _{DS(on)} Flatness	V+ = 2.5 V	Room		2		52
Switch Off	I _{S(off)}	V+ = 5.5 V, V _S = 1 V/4.5 V, V _D = 4.5 V/1 V	Room Full	- 1.0 - 4.0		1.0 4.0	
Leakage Current	I _{D(off)}	V = 0.0 V, Vg = 1 V/ 1.0 V, V _D = 1.0 V/ 1 V	Room Full	- 1.0 - 4.0		1.0 4.0	nA
Channel-On Leakage Current	I _{D(on)}	$V+ = 5.5 V$, $V_S = V_D = 1 V/4.5 V$	Room Full	- 1.0 - 3.0		1.0 4.5	
Digital Control							
Input High Voltage	V_{INH}		Full	2.4			V
Input Low Voltage	V_{INL}		Full			0.8	\ \ \
Input Capacitance	C _{in}		Full		3		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ
Dynamic Characteristics	•		•				
Turn-On Time ^d	t _{ON}	V 2*V 2 V D 200 0 C 25 aF	Room Full		9	11 15	
Turn-Off Time ^d	t _{OFF}	V_D or V_S = 3 V, R_L = 300 Ω , C_L = 35 pF Figure 1 and 2	Room Full		5	7 9	ns
Break-Before-Make Time ^d	t_d		Room	1	4		
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_S = 0 V, V_{GEN} = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	рС
Off-Isolation ^d	OIRR	D 5000 5 x5 1 MHz	Room		- 73		-10
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 70		dB
Source-Off Capacitance ^d	C _{S(off)}		Room		7		
Channel-On Capacitance ^d	C _{D(on)}	$V_{IN} = 0$ or V_{+} , $f = 1$ MHz	Room		20		рF
Drain-to-Source Capacitance ^d	C _{DS(off)}	· IIV	Room		20		ρ'
Power Supply							
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	l+	V _{IN} = 0 or V+			0.01	1.0	μΑ
Power Consumption	P_{C}	VIN - O OI VI				0.6	μW

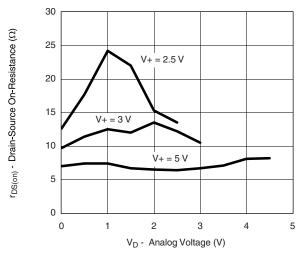
Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Guaranteed by 5 V leakage testing, not production tested.

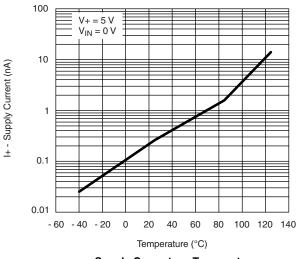
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



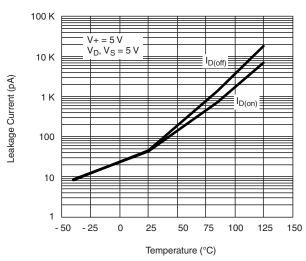
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



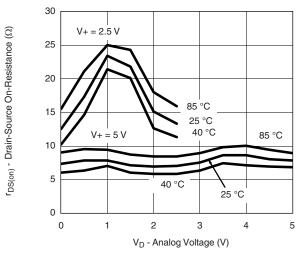
r_{DS(on)} vs. Analog and Power Voltage



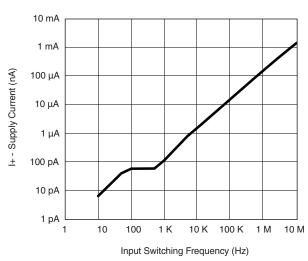
Supply Current vs. Temperature



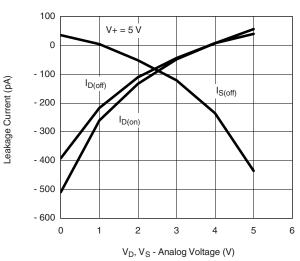
Leakage Current vs. Temperature



r_{DS(on)} vs. Analog Voltage and Temperature



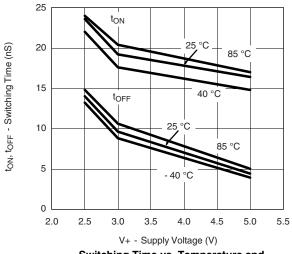
Supply Current vs. Input Switching Frequency



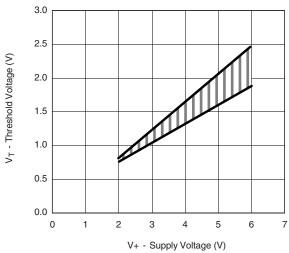
Leakage vs. Analog Voltage

VISHAY

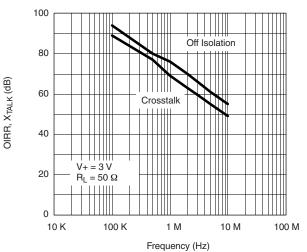
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



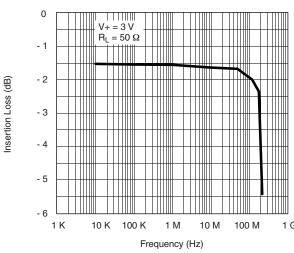
Switching Time vs. Temperature and Supply Voltage



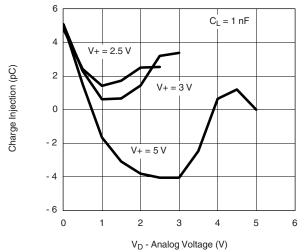
Input Switching Threshold vs. Supply Voltage



Crosstalk and Off Isolation vs. Frequency



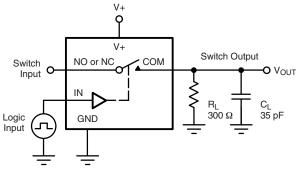
Insertion Loss vs. Frequency



Charge Injection vs. Analog Voltage

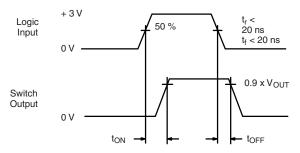


TEST CIRCUITS



C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

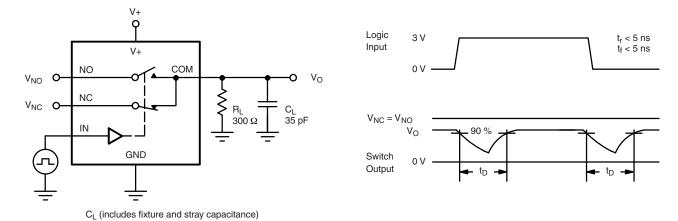


Figure 2. Break-Before-Make Interval

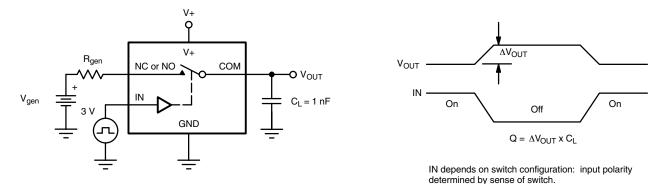


Figure 3. Charge Injection

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TEST CIRCUITS

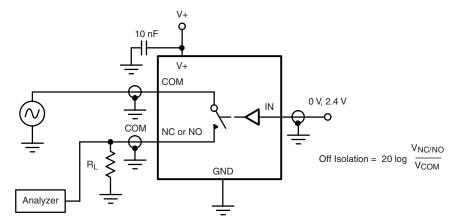


Figure 4. Off-Isolation

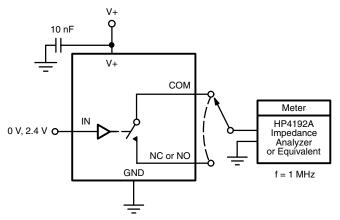


Figure 5. Channel Off/On Capacitance

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SC-70: 6-LEADS





Dim	MIL	LIMET	ERS	INCHES			
	Min	Nom	Max	Min	Nom	Max	
Α	0.90	-	1.10	0.035	_	0.043	
A ₁	-	-	0.10	-	-	0.004	
A_2	0.80	-	1.00	0.031	-	0.039	
b	0.15	-	0.30	0.006	_	0.012	
С	0.10	-	0.25	0.004	_	0.010	
D	1.80	2.00	2.20	0.071	0.079	0.087	
Ε	1.80	2.10	2.40	0.071	0.083	0.094	
E ₁	1.15	1.25	1.35	0.045	0.049	0.053	
е	0.65BSC 0.026BSC						
e ₁	1.20	1.30	1.40	0.047	0.051	0.055	
L	0.10	0.20	0.30	0.004	0.008	0.012	
9		7°Nom			7°Nom		



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Vishay

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